

Abstract of the Invention

[0053] A method for planarizing an organosilicate layer is provided. The organosilicate material layer is planarized using a slurry in conjunction with a chemical mechanical polishing (CMP) process. The slurry comprises an abrasive material dispersed in a suitable solvent. The slurry preferably has a pH greater than about 9. The abrasive material preferably has an average particle size greater than about 35 nm (nanometers).